

CBRHD SERIES

**HIGH DENSITY SURFACE MOUNT
½ AMP DUAL IN LINE
BRIDGE RECTIFIER**

FEATURES:

- Truly efficient use of board space, requires only 42mm² of board space vs. 120mm² of board space for industry standard 1.0 Amp surface mount bridge rectifier.
- 50% higher density (amps/mm²) than the industry standard 1.0 Amp surface mount bridge rectifier.
- Glass passivated chips for high reliability.

**HDTM
BRIDGE**



HDDIP CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHD series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL	CBRHD -02	CBRHD -04	CBRHD -06	CBRHD -10*	UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	200	400	600	1000	V
DC Blocking Voltage	V _R	200	400	600	1000	V
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	700	V
Average Forward Current (T _A =40°C)(1)	I _O			0.5		A
Average Forward Current (T _A =40°C)(2)	I _O			0.8		A
Peak Forward Surge Current	I _{FSM}			30		A
Operating and Storage Junction Temperature	T _J , T _{stg}		-65 to +150			°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V _F	I _F =400mA (Per Diode)			1.0	V
I _R	V _R =Rated V _{RRM}			5.0	μA
I _R	V _R =Rated V _{RRM} , T _A =125°C			500	μA
C _J	V _R =4.0V, f=1.0MHz		20		pF

(1) Mounted on a Glass-Epoxy P.C.B.

(2) Mounted on a Ceramic P.C.B.

*Available on special order, please consult factory.

All dimensions in inches (mm).

TOP VIEW

